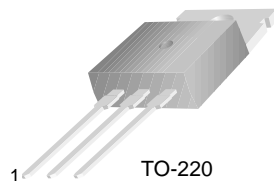


KSC5367

KSC5367

High Voltage and High Reliability

- High speed Switching
- Wide Safe Operating Area
- High Collector Base Voltage



TO-220
1.Base 2.Collector 3.Emitter

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	1600	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	3	A
I_{CP}	*Collector Current (Pulse)	6	A
I_B	Base Current	2	A
I_{BP}	*Base Current (Pulse)	4	A
P_C	Power Dissipation($T_C=25$)	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

* Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

Thermal Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	1.56	$^\circ\text{C/W}$
$R_{\theta ja}$		Junction to Ambient	62.5	

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1\text{mA}, I_E = 0$	1600	-	-	V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}, I_B = 0$	800	-	-	V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_C = 0.5\text{mA}, I_C = 0$	12	-	-	V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 1,600\text{V}, I_E = 0$	-	-	20	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 12\text{V}, I_C = 0$	-	-	20	μA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 3\text{V}, I_C = 0.4\text{A}$ $V_{CE} = 10\text{V}, I_C = 5\text{mA}$	12 8	- -	35 -	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = 250\text{mA}, I_B = 25\text{mA}$	-	-	2.5	V
		$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	-	4.5	V
		$I_C = 1\text{A}, I_B = 0.2\text{A}$	-	-	2.5	V
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage	$I_C = 3\text{A}, I_B = 0.6\text{A}$	-	-	1.5	V
C_{ob}	Output Capacitance	$I_C = 500\text{mA}, I_B = 50\text{mA}$	-	40		pF
t_{ON}	Turn ON Time	$V_{CC} = 125\text{V}, I_C = 0.5\text{A}$ $I_{B1} = 42\text{mA}, I_{B2} = -333\text{mA}$ $R_L = 250\Omega$	-	-	0.5	μs
t_{STG}	Storage Time		-	-	2.2	μs
t_F	Fall Time		-	-	0.5	μs
t_{ON}	Turn ON Time	$V_{CC} = 250\text{V}, I_C = 1\text{A}$ $I_{B1} = 0.2\text{A}, I_{B2} = -0.4\text{A}$ $R_L = 250\Omega$	-	-	0.5	μs
t_{STG}	Storage Time		-	-	4.0	μs
t_F	Fall Time		-	-	0.5	μs

Typical Characteristics

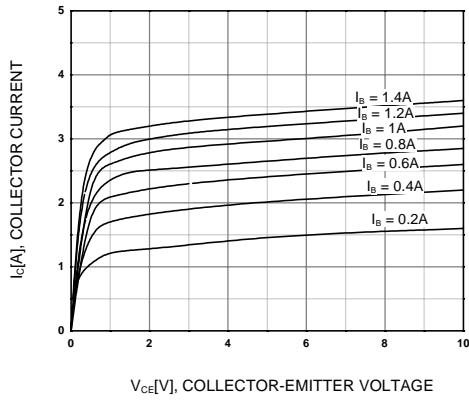


Figure 1. Static Characteristic

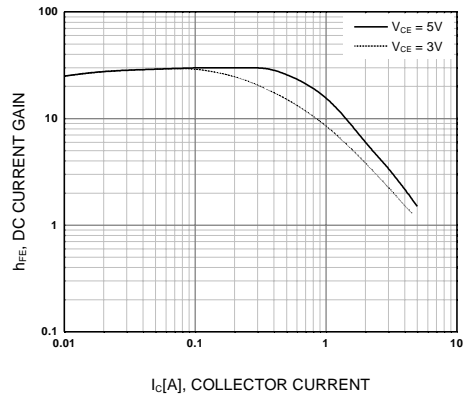


Figure 2. DC current Gain

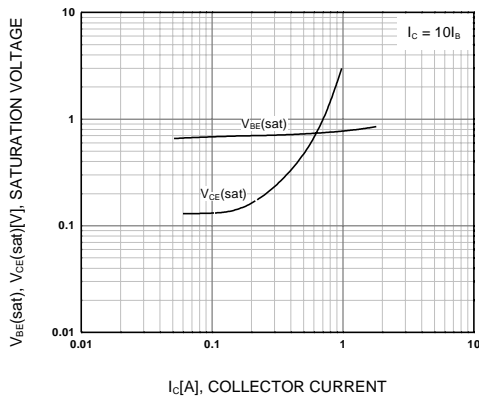


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

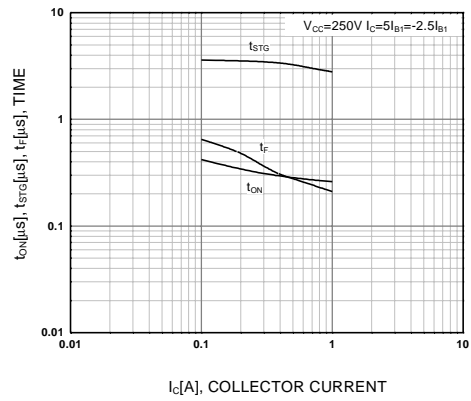


Figure 4. Switching Time

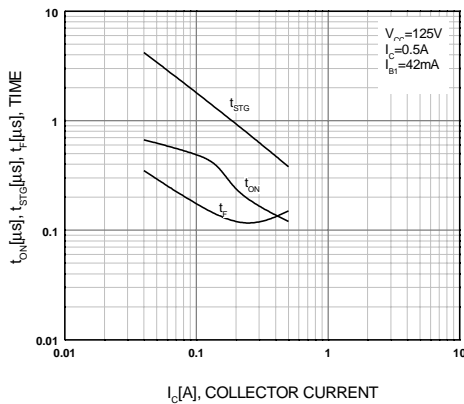


Figure 5. Switching Time

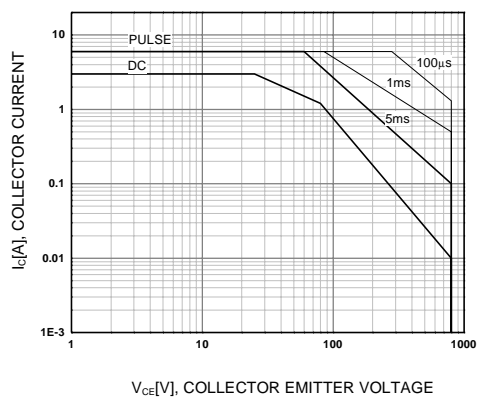


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

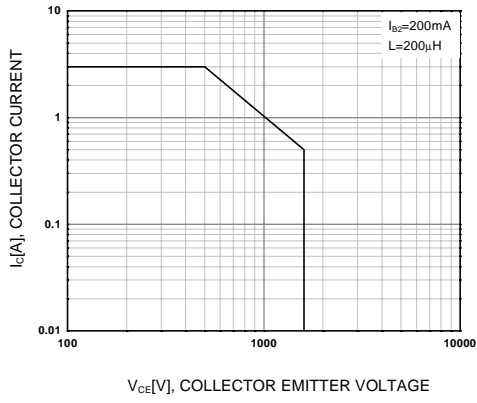


Figure 7. Reverse Bias Safe Operating Area

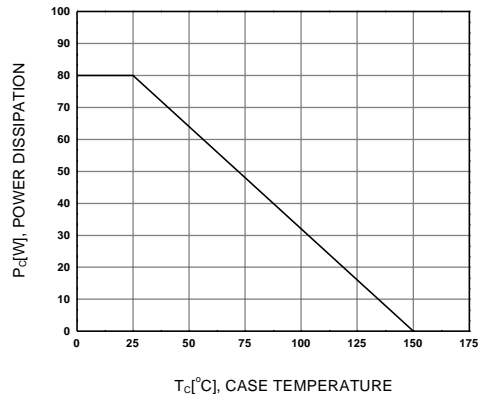
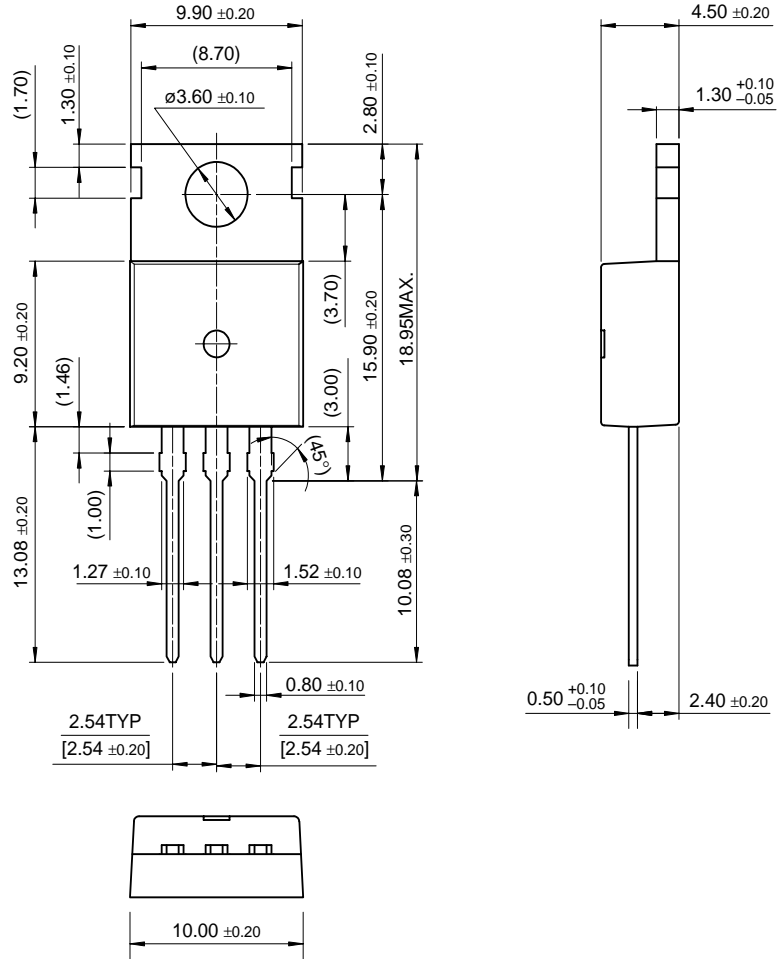


Figure 8. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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